

# Supplemental Material

## Electronic and electrocatalytic properties of PbTiO<sub>3</sub>: Unveiling the effect of strain and oxygen vacancy

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## The effect of single oxygen vacancy on tetragonal $\text{PbTiO}_3$

To reduce the artificial self-image interactions imposed by periodic-boundary conditions<sup>1</sup> in a single-defect structure, some convergence tests were done on a number of enlarged supercells, namely 5-atoms ( $1 \times 1 \times 1$ ), 40-atoms ( $2 \times 2 \times 2$ ), 136-atoms ( $3 \times 3 \times 3$ ), and 256-atoms ( $4 \times 4 \times 4$ ). We have sampled the Brillouin zone with a  $\mathbf{k}$ -mesh considering  $12 \times 12 \times 11$ ,  $6 \times 6 \times 5$ , and  $3 \times 3 \times 2$ , and  $2 \times 2 \times 1$   $\mathbf{k}$  meshes for supercells containing 5, 40, 136, and 256 atoms, respectively. To reveal the energetically most preferable single-defect structure, the formation energy  $E_f$  was obtained following the formula:<sup>2</sup>

$$E_f = E(V_O - \text{PbTiO}_3) - E(\text{PbTiO}_3) + N_O \mu_O \quad (1)$$

We have found that supercells containing 136 atoms are sufficiently large to obtain defect formation energies that converged satisfactorily (see Figure S1). This size minimizes the interaction of the vacancy with its own image in the neighboring cells. The chemical potential is used as the thermodynamic natural variable throughout all expressions for the defect formation energy and solution enthalpy. The chemical potentials of Ti, Pb, and O atoms are not independent of each other, they obey a number of restrictions based on energetic equilibrium (see Figure S6). Such conditions maintain a stable  $\text{PbTiO}_3$  compound. This includes:

$$\Delta\mu_{\text{Ti}} + \Delta\mu_{\text{Pb}} + 3\Delta\mu_{\text{O}} = \Delta E(\text{PbTiO}_3) = -2.5060 \text{ eV} \quad (2)$$

where  $\mu_{\text{Ti}}$ ,  $\mu_{\text{Pb}}$ , and  $\mu_{\text{O}}$  are the chemical potentials of Ti, Pb, and O.  $\Delta E(\text{PbTiO}_3)$  is the corresponding formation enthalpy. Other conditions that enforce the formation of single crystal compound  $\text{PbTiO}_3$  with no secondary precipitate like  $\text{PbO}$ ,  $\text{PbO}_2$ ,  $\text{Ti}_2\text{O}$ , and  $\text{Ti}_3\text{O}_5$ .

Equation 2:  $\Delta\mu_{Ti} + 2\Delta\mu_{Pb} \geq -2.5060\text{eV}$

Equation 3:  $-0.333\Delta\mu_{Ti} + 0.666\Delta\mu_{Pb} \leq -0.2267\text{eV}$

Equation 4:  $-1.333\Delta\mu_{Ti} + 1.666\Delta\mu_{Pb} \leq 1.8933\text{eV}$

Equation 5:  $-0.666\Delta\mu_{Ti} + 0.333\Delta\mu_{Pb} \leq 0.3707\text{eV}$

Equation 6:  $1.333\Delta\mu_{Ti} - 1.666\Delta\mu_{Pb} \leq 0.7957\text{eV}$

Equation 7:  $1.666\Delta\mu_{Ti} - 0.333\Delta\mu_{Pb} \leq -1.2007\text{eV}$

Equation 8:  $2.666\Delta\mu_{Ti} - 0.333\Delta\mu_{Pb} \leq -0.7347\text{eV}$

Equation 9:  $5.666\Delta\mu_{Ti} - 0.333\Delta\mu_{Pb} \leq -0.0817\text{eV}$

Equation 10:  $3.000\Delta\mu_{Ti} + \Delta\mu_{Pb} \leq -0.0600\text{eV}$

We have studied the effect of an oxygen vacancy ( $V_O$ ) in the tetragonal structure of  $\text{PbTiO}_3$ . This single vacancy could play the role of an intrinsic defect, having critical impacts on the evolution of the physical properties. The aim of this section is to analyze the effect of the incorporation of oxygen vacancies on the exciton binding energy. Compared to the case displayed in Figure S5, the incorporation of  $V_O$  in our structure yields a decrease of the band gap. This is because the oxygen vacancy is singly ionized<sup>3</sup> and thus affects the transport properties of  $\text{PbTiO}_3$ . The calculation of the formation gives energy a value  $E_f = -0.947$  eV/atom, in good agreement with the value of  $-0.97$  eV/atom found in Ref.<sup>4</sup> where  $E(V_O - \text{PbTiO}_3)$  and  $E(\text{PbTiO}_3)$  are the total energies of defective and perfect structures, respectively.  $\mu_0$  is the atomic chemical potential of oxygen, and  $N_0$  is the number of  $V_O$  in the cell. According to the PDOS plot of  $V_O$ - $\text{PbTiO}_3$  (see Figure S9), We can see a weak shift of Ti  $3d$  orbital towards the Fermi level. This can be attributed to the fact that a change of electronic configuration from  $3d^0$  to  $3d^2$  occurs with localized states in the band gap. Correspondingly, the valence state of the Ti ion is expected to change from  $+4$  to  $+2$ . This is because the Ti ion accepts two electrons from the oxygen vacancy. According to the result summarized in Table S1, the calculation of exciton-binding energy for the  $V_O$  structure is found to be very moderate,  $E_b = 53$  meV, in good agreement with most organic-inorganic

metal halide perovskites.<sup>5</sup>

## The hydrogen adsorption Gibbs free energy

In this study, the solvation effect is not taken into account due to the slight influence on the properties of HER. The hydrogen adsorption Gibbs free energy ( $\Delta G_H$ ) was calculated as follow:<sup>2</sup>

$$\Delta G_{H^*} = \Delta E^{H^*} - T\Delta S + \Delta E^{ZPE} \quad (3)$$

where  $T\Delta S$  is the entropy difference between adsorbed  $H^*$  and  $H_2$  in gas phase at 298.15 K, and  $\Delta E^{H^*}$  is the differential hydrogen adsorption energy

$$\Delta G_{H^*} = E^{PbTiO_3@H} - E^{PbTiO_3} - \frac{1}{2}E(H_2) \quad (4)$$

with  $E^{PbTiO_3@H}$ ,  $E^{PbTiO_3}$  and  $\frac{1}{2}E(H_2)$  representing the total energies with one hydrogen atom adsorbed on the surface, the energy of the pristine surface and  $H_2$  molecule, respectively.  $\Delta E^{ZPE}$  is the difference in zero-point energy between adsorbed  $H^*$  and molecular  $H_2$  in the gas phase, which could be calculated as

$$\Delta E^{ZPE} = \Delta E^{ZPE}(H^*) - \frac{1}{2}\Delta E^{ZPE}(H_2) \quad (5)$$

$E^{ZPE}(H^*)$  being the zero-point energy of one adsorbed  $H^*$  on the catalyst obtained by  $\frac{1}{2}h\nu$  without the contributions of the catalyst, and  $E^{ZPE}(H_2)$  is the zero-point energy of the molecular  $H_2$  in gas phase.

**Table S1** Calculated band gap of PbTiO<sub>3</sub> using GGA + *U*, GGA + *U* + SOC, and G<sub>0</sub>W<sub>0</sub>. The results are compared to previous theoretical and experimental results. The table also contains the effective masses of the holes ( $m_h^*(m_0)$ ) and electrons ( $m_e^*(m_0)$ ), the recombination rate ( $m_h^*/m_e^*$ ), and the exciton binding energy ( $E_b$ ) (meV). The values <sup>WM</sup> and <sup>BSE</sup> correspond to those calculated using the two-band Wannier–Mott and quasi-particle-BSE correction model. The macroscopic dielectric function  $\epsilon_\infty$  has been computed within the standard random-phase approximation (RPA), and the effective masses of carriers have been extracted from band structures of the Wannier function. (0%) and ( $\pm 5\%$ ) correspond respectively to pristine and strained structures. The effective masses, the macroscopic dielectric function  $\epsilon_\infty$  and the exciton binding energy ( $E_b$ ) are calculated with the G<sub>0</sub>W<sub>0</sub> approach

	$E_g$ (eV)	$m_h^*(m_0)$	$m_e^*(m_0)$	$m_h^*/m_e^*$	$\epsilon_\infty$	$E_b$ (meV)
(0%)	2.95	1.19 <sup>a</sup> , 0.87 <sup>b</sup>	2.07 <sup>c</sup> , 1.68 <sup>d</sup>	0.46	6.99	185 <sup>WM</sup> /172 <sup>BSE</sup>
(-5%)	2.63	1.07 <sup>a</sup> , 1.25 <sup>b</sup>	2.46 <sup>c</sup> , 1.09 <sup>d</sup> , 73.64 <sup>f</sup>	0.045	6.44	360 <sup>WM</sup> /320 <sup>BSE</sup>
(+5%)	2.93	1.85 <sup>a</sup> , 1.68 <sup>b</sup>	1.63 <sup>g</sup> , 1.67 <sup>i</sup>	1.67	6.66	261 <sup>WM</sup>
V <sub>O</sub>	1.30	2.25 <sup>j</sup> , 10.51 <sup>k</sup>	0.77 <sup>l</sup> , 2.70 <sup>m</sup>	3.66	18.72	53 <sup>WM</sup>
GGA + <i>U</i> + SOC (0%)	2.93	–	–	–	–	–
G <sub>0</sub> W <sub>0</sub> (0%)	2.89	–	–	–	–	–
Exprt <sup>?</sup> (0%)	3.097	–	–	–	–	–

<sup>a</sup> corresponds to the X  $\rightarrow$  M direction

<sup>b</sup> corresponds to the X  $\rightarrow$   $\Gamma$  direction

<sup>c</sup> corresponds to the Z  $\rightarrow$  A direction

<sup>d</sup> corresponds to the Z  $\rightarrow$  R direction

<sup>f</sup> corresponds to the Z  $\rightarrow$   $\Gamma$  direction

<sup>g</sup> corresponds to the  $\Gamma$   $\rightarrow$  X direction

<sup>i</sup> corresponds to the  $\Gamma$   $\rightarrow$  M direction

<sup>j</sup> corresponds to the A  $\rightarrow$  Z direction

<sup>k</sup> corresponds to the A  $\rightarrow$  R direction

<sup>l</sup> corresponds to the M  $\rightarrow$  X direction

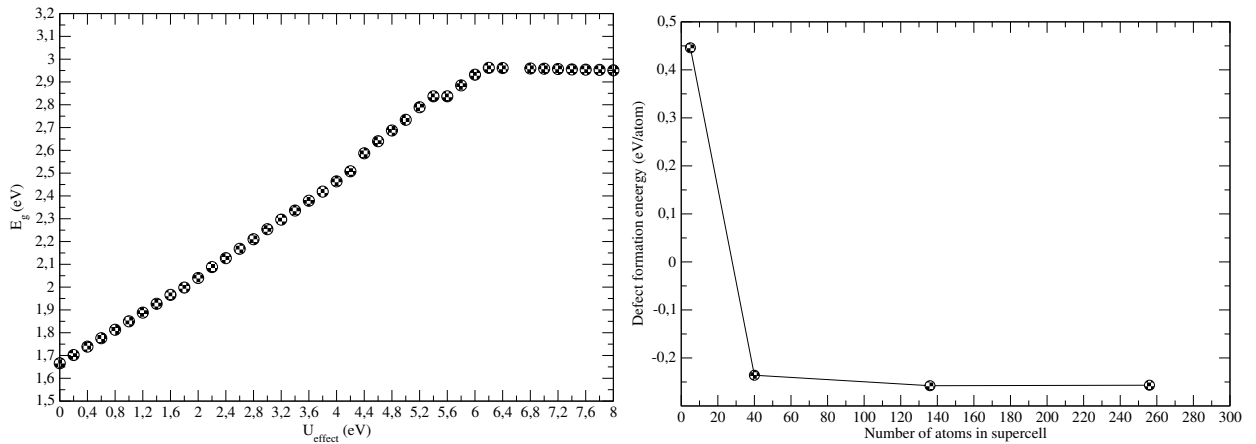
<sup>m</sup> corresponds to the A  $\rightarrow$   $\Gamma$  direction

**Table S2** Energy adsorption of the selected tested active sites, the number corresponding to the case plotted in Figure S4.

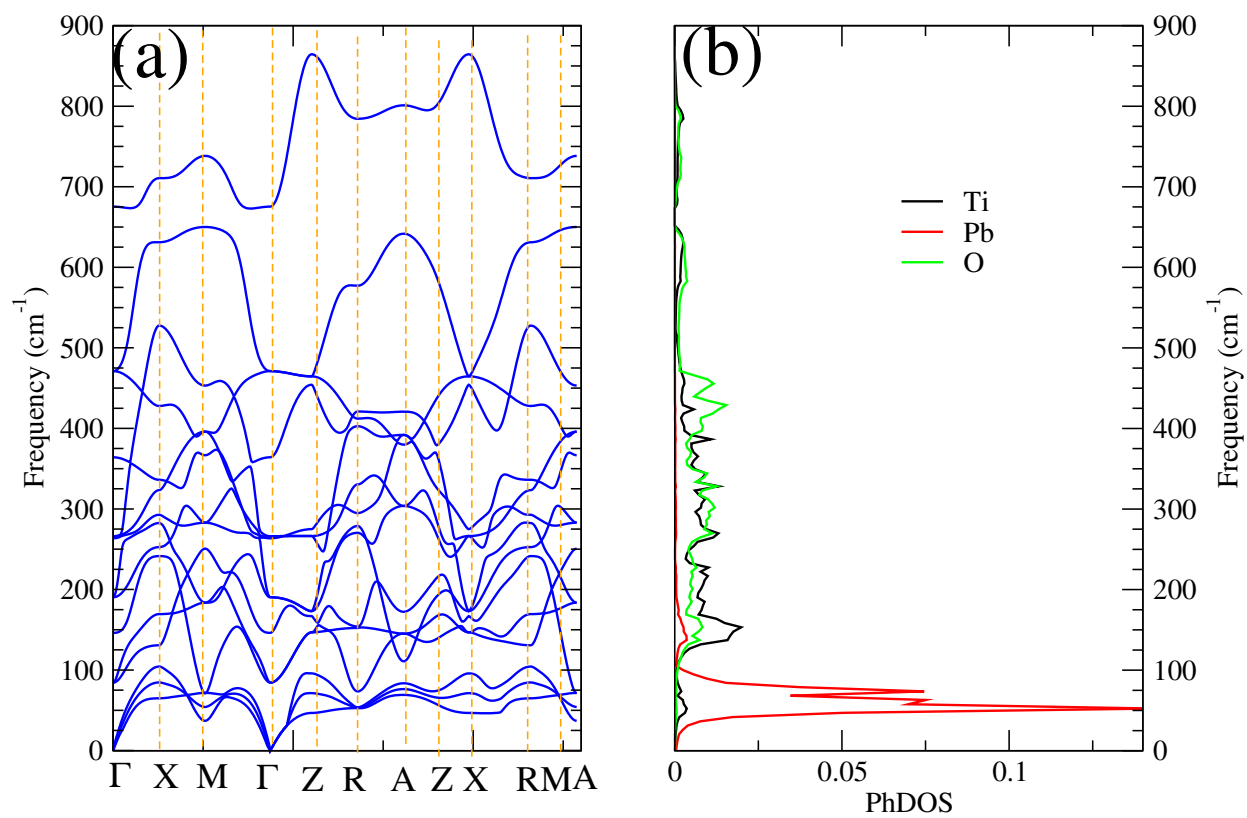
case	$E_{ads}$ (eV)
(1)	-0.2003
(2)	-0.7456
(3)	-1.7203
(4)	-0.9364
(5)	-1.3439
(6)	-0.1618

**Table S3** Energy adsorption and HER values of the pristine, structure under compression, tensile, and oxygen vacancy defective structures

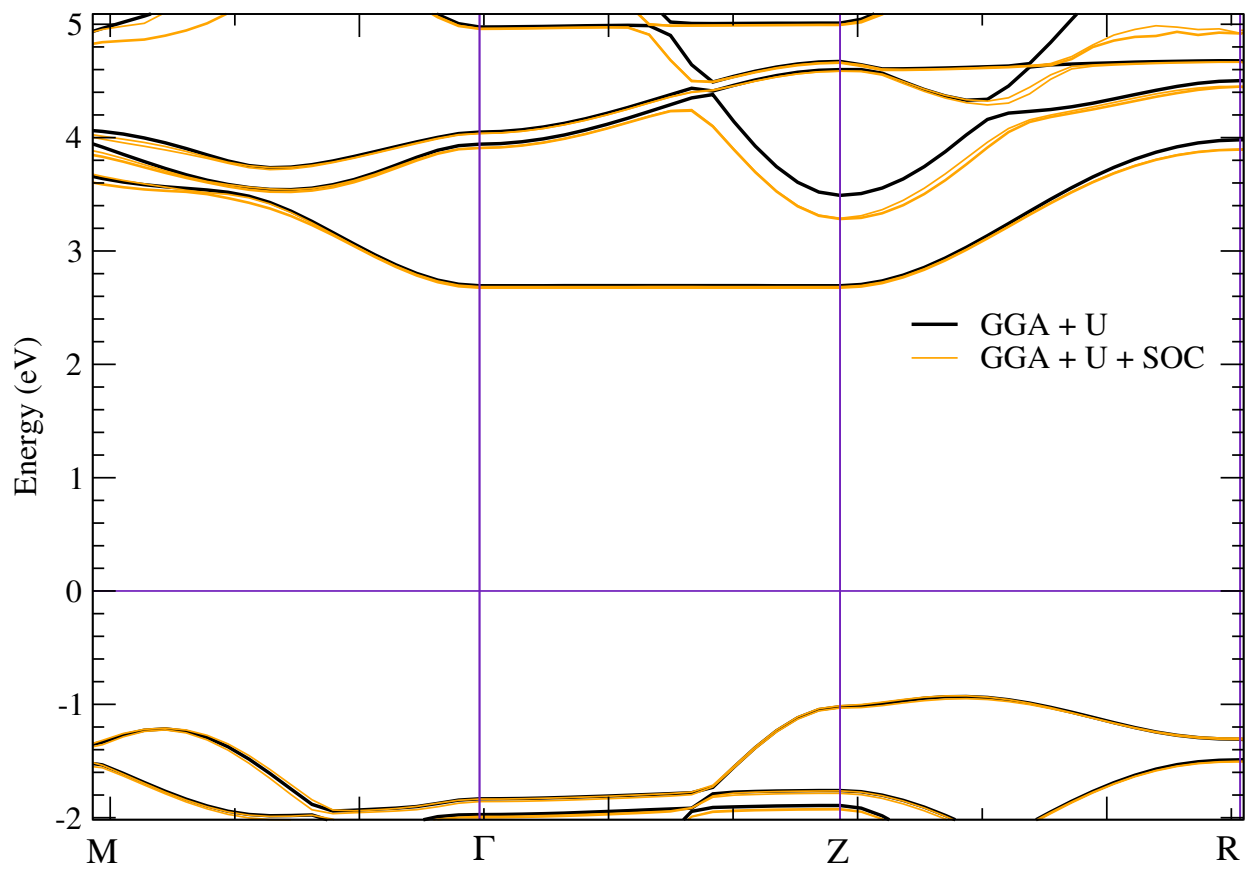
case	$E_{ads}$ (eV)	HER (eV)
Pristine (0%)	-1.7281	-1.48
compression (-5%)	-2.3166	-2.01
tensile (+5%)	-1.9181	-1.67
$V_O$	-0.2508	-0.03



**Figure S1** (Color online) Left panel: the optimization of Hubbard correction  $U_{effect}=U-J$  as a function of band gap  $E_g$ . Right panel: Ab initio calculations of the single-site defect formation energies of oxygen vacancy against the size of the supercell.

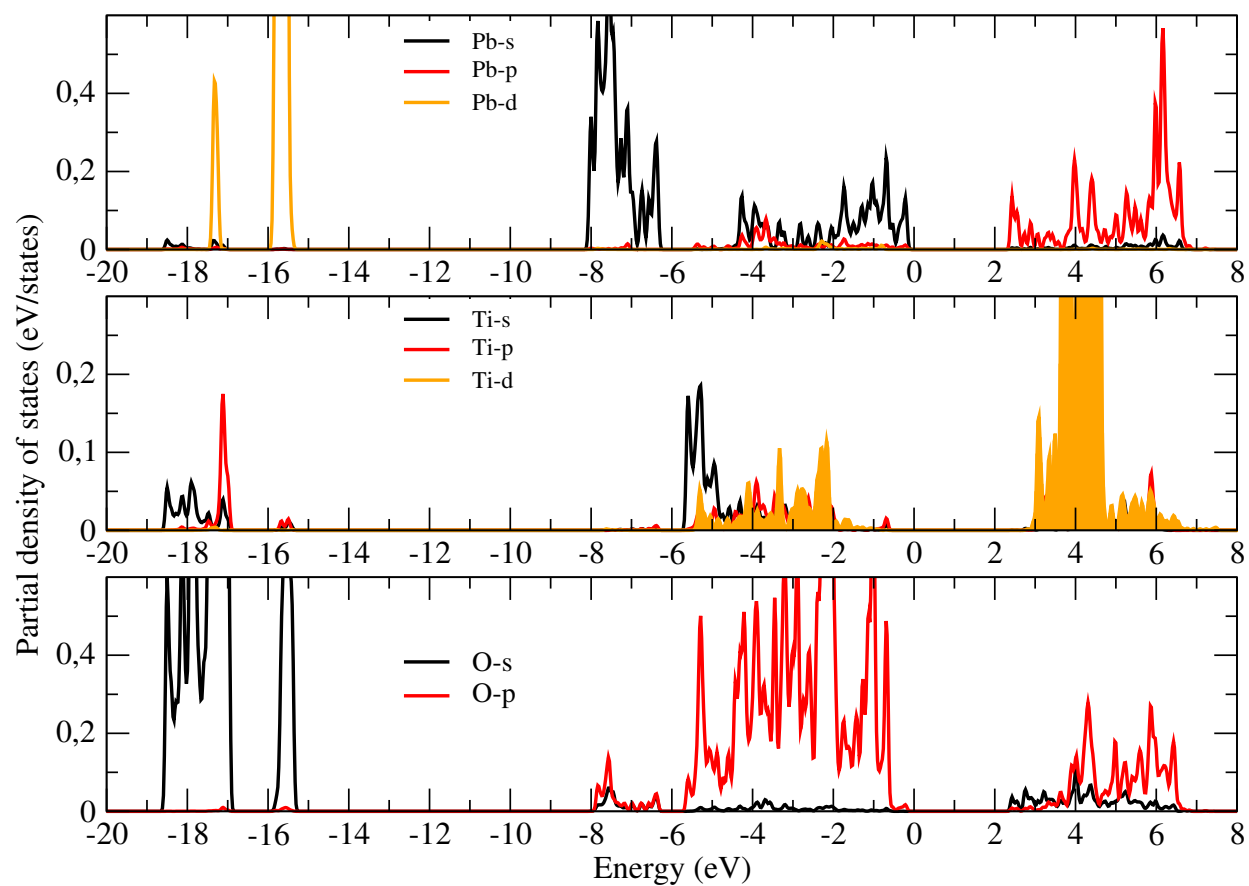


**Figure S2** (Color online) (a) Calculated Phonon dispersion and (b) Calculated phonon density of states (PhDOS).

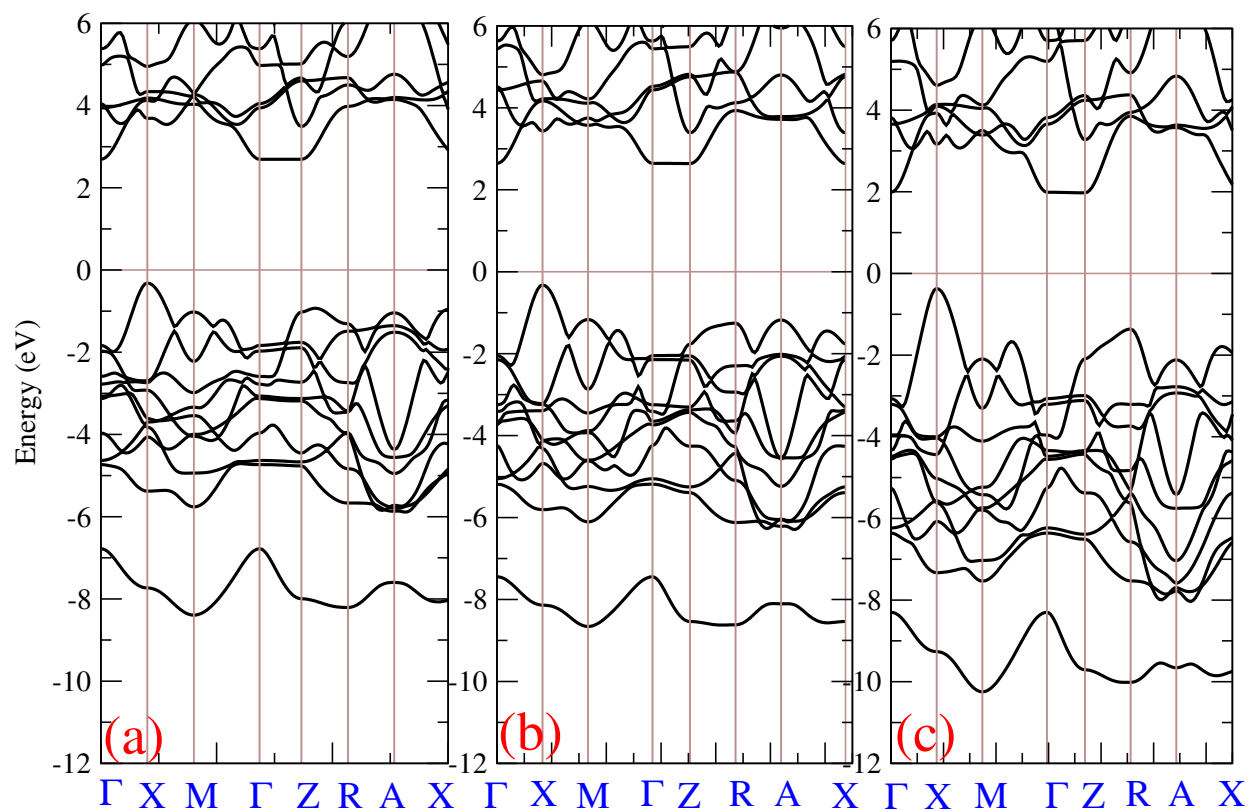


**Figure S3** (Color online) a Zoom on the Band structure calculation along the  $M \rightarrow \Gamma \rightarrow Z \rightarrow R$  directions at GGA +  $U$  and GGA +  $U$  + SOC levels

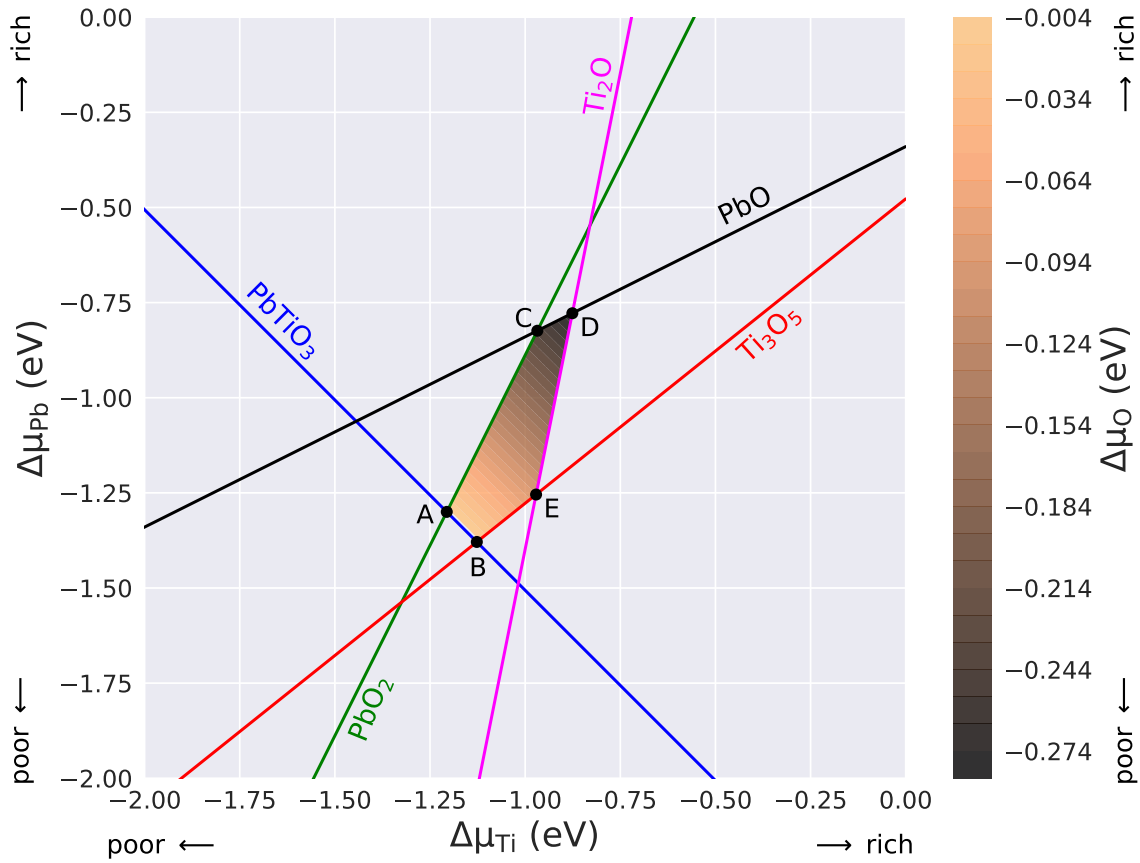




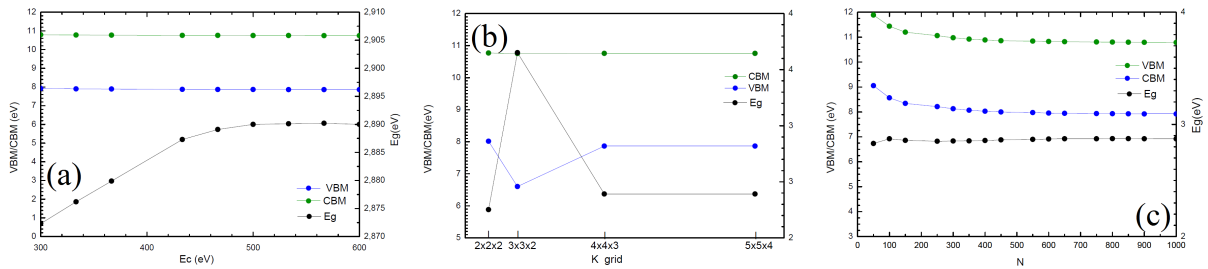
**Figure S4** (Color online) Projected densities of states (PDOS) of pristine PbTiO<sub>3</sub> at GGA +  $U$ .



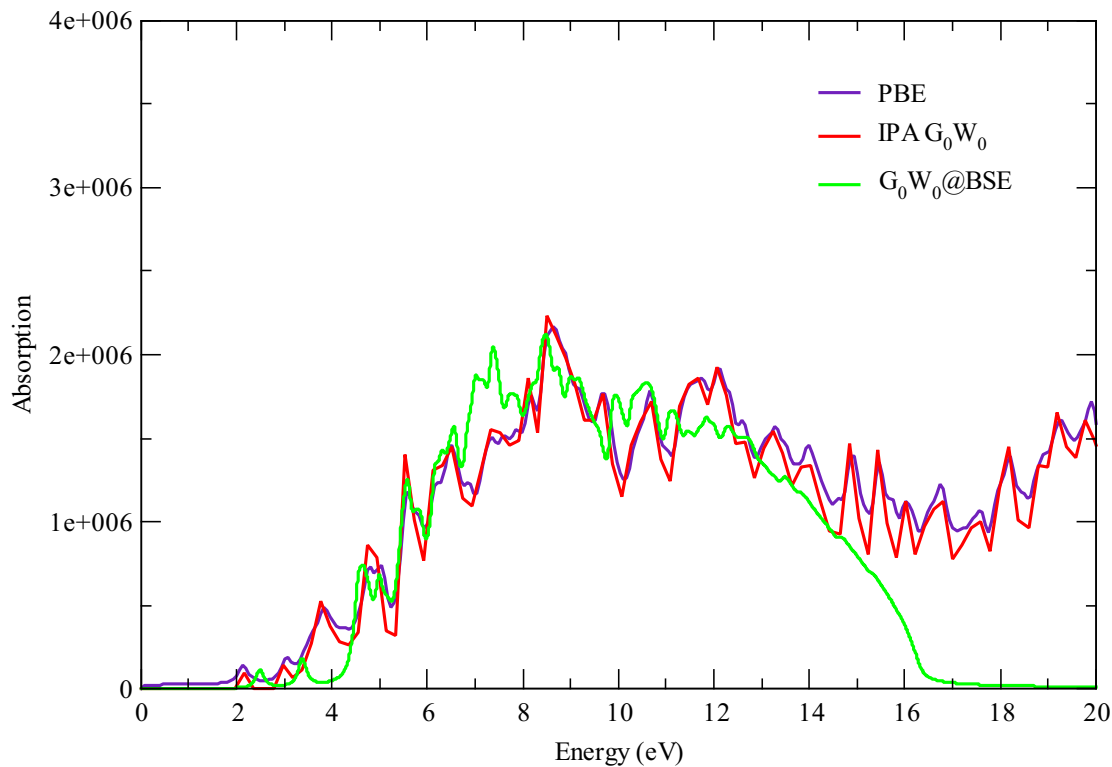
**Figure S5** (Color online) band structure evolution of strained structures for (a) 0%, (b) -5%, and (c) -7%, at GGA +  $U$  level. (0%) correspond to pristine and (-5%) and (-7%) to strained structures.



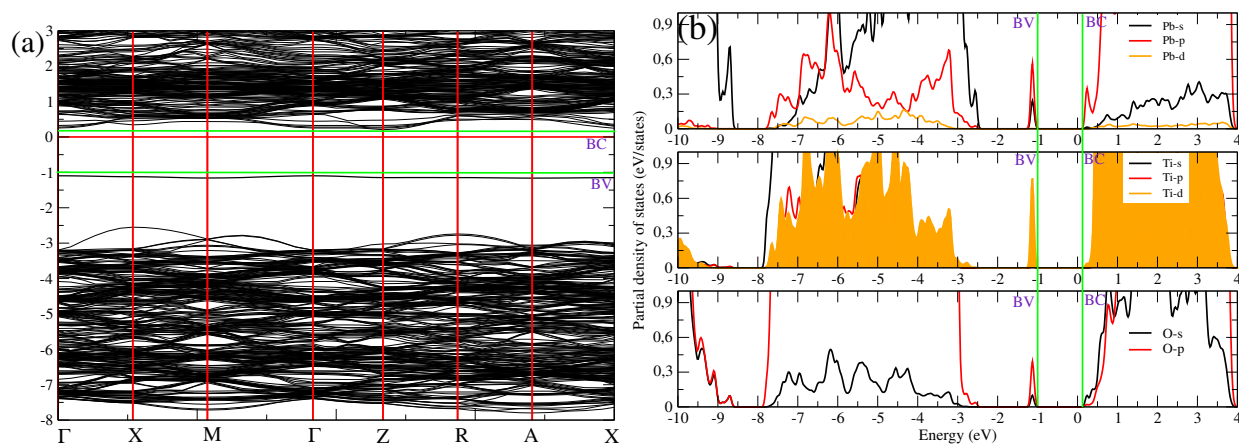
**Figure S6** (Color online) Chemical potential phase diagram showing the region of stability of defective  $\text{PbTiO}_3$ . We show the variation in  $\Delta\mu_{Ti}$ , as a function of  $\Delta\mu_{Pb}$  and  $\Delta\mu_O$  within the stability region. Color lines are the limits imposed by competing phases. A, B, C, D, and E delimit the stability area.



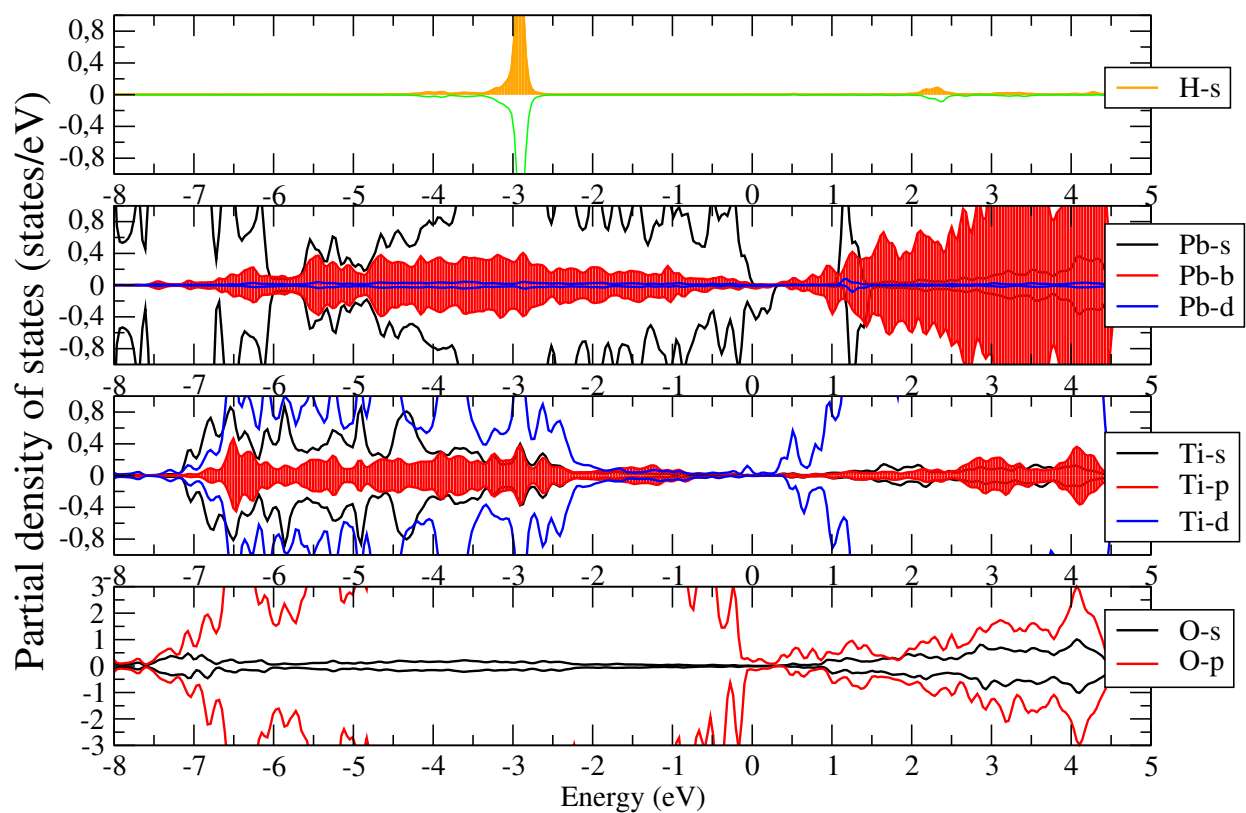
**Figure S7** (Color online) Convergence of the band energy and band gap of  $\text{PbTiO}_3$  with respect to (a) the energy cutoff of the response function  $E_c$  at  $\Gamma$  Points of GW calculations, (b) k grid and (c) the number of empty states  $N$ . The convergence behaviour is insensitive for k mesh  $4 \times 4 \times 3$  and  $N=800$  and  $E_c=600$  eV



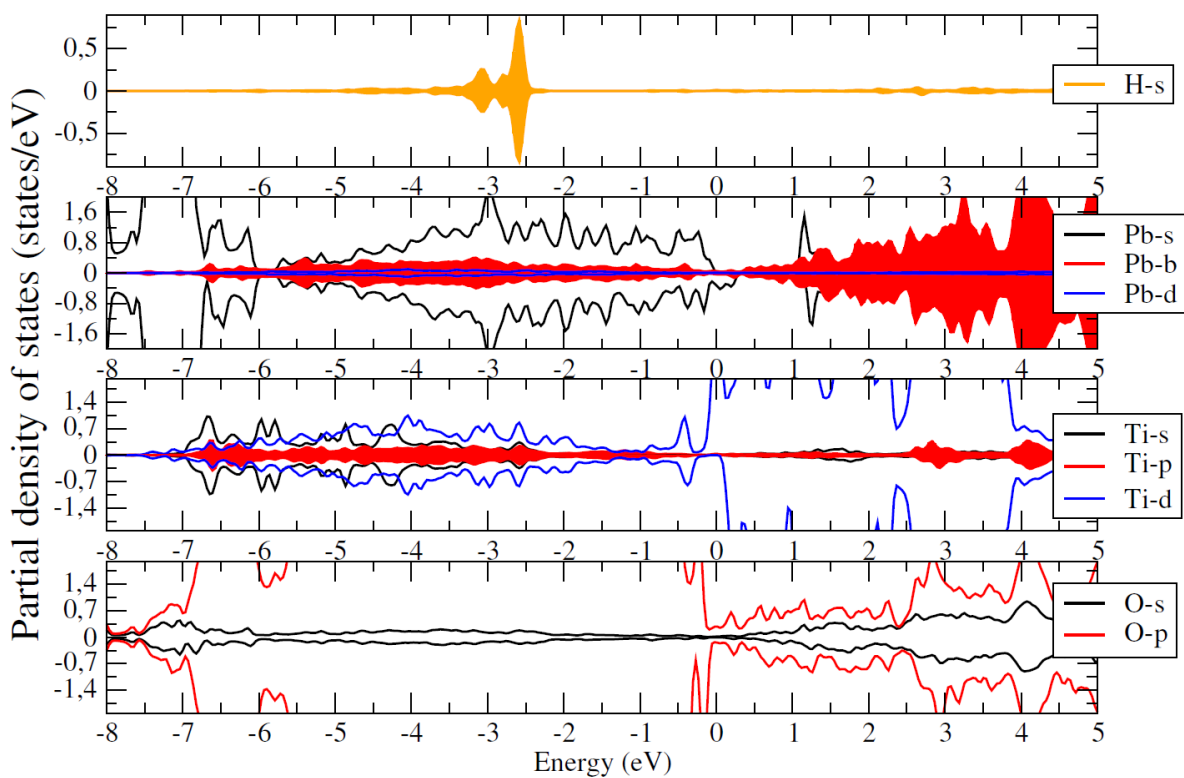
**Figure S8** (Color online) The calculated absorption spectrum within PBE, IPA@GGA +  $U$ , and GW@BSE approaches.



**Figure S9** (Color online) (a) Band structure and (b) PDOS of the 136-atoms ( $3 \times 3 \times 3$ )  $V_O$ - $PbTiO_3$  structure at the GGA +  $U$  level.



**Figure S10** (Color online) Projected densities of states (PDOS) of the strained compressive (-5%) structure of  $\text{PbTiO}_3$  compound at GGA +  $U$  level.



**Figure S11** (Color online) Projected densities of states (PDOS) of the defective VO slab structure of  $\text{PbTiO}_3@H$  compound at the GGA +  $U$  level.

## References

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